WHAT IS CLAIMED IS:

1. A light emitting device comprising:

a plurality of pixels arranged in a matrix, each of the plurality of pixels comprising a switching element and a light emitting element; and

a plurality of source signal lines for supplying signals to the switching element,

wherein at least one of the plurality of source signal lines comprises a conductor and a conductive coating on the conductor.

2. A light emitting device according to claim 1, wherein the conductive coating is formed by an electroplating method.

3. A light emitting device according to claim 1, wherein the conductive coating comprises at least one selected from the group consisting of Cu, Al, Au, Ag, and an alloy thereof as a main component.

4. A light emitting device according to any one of claims 1, wherein the conductor is made of the same material as a gate electrode of the switching element.

5. A light emitting device according to claim 1, wherein the switching element comprises at least one thin film transistor.

6. An electronic appliance comprising the light emitting device according to claim 1, wherein the light emitting device is selected from the group consisting of an

electroluminescence display device, a personal computer, and a digital versatile disk.

7. A light emitting device comprising:

a plurality of pixels arranged in a matrix, each of the plurality of pixels comprising a switching element and a light emitting element; and

a plurality of power supply lines for supplying potentials to the light emitting element,

wherein at least one of the plurality of power supply lines comprises a conductor and a conductive coating on the conductor.

8. A light emitting device according to claim 7, wherein the conductive coating is formed by an electroplating method.

9. A light emitting device according to claim 7, wherein the conductive coating comprises at least one selected from the group consisting of Cu, Al, Au, Ag, and an alloy thereof as a main component.

10. A light emitting device according to any one of claims 7, wherein the conductor is made of the same material as a gate electrode of the switching element.

11. A light emitting device according to claim 7, wherein the switching element comprises at least one thin film transistor.

12. An electronic appliance comprising the light emitting device according to claim 7,

wherein the light emitting device is selected from the group consisting of an electroluminescence display device, a personal computer, and a digital versatile disk.

13. A light emitting device comprising:

a plurality of pixels arranged in a matrix, each of the plurality of pixels comprising a switching element and a light emitting element;

a plurality of source signal lines for supplying signals to the switching element; and

a plurality of power supply lines for supplying potentials to the light emitting element,

wherein at least one of the plurality of source signal lines comprises a first conductor and a first conductive coating on the first conductor, and

wherein at least one of the plurality of power supply lines comprises a second conductor and a second conductive coating on the second conductor.

14. A light emitting device according to claim 13, wherein at least one of the first conductive coating and the second conductive coating is formed by an electroplating method.

15. A light emitting device according to claim 13, wherein at least one of the first conductive coating and the second conductive coating comprises at least one selected from the group consisting of Cu, Al, Au, Ag, and an alloy thereof as a main component.

16. A light emitting device according to claim 13, wherein the first conductor and the second conductor are simultaneously formed.

17. A light emitting device according to claim 13, wherein at least one of the first conductive coating and the second conductive coating is made of the same material as a gate electrode of the switching element.

18. A light emitting device according to any one of claims 13, wherein at least one of the first conductive coating and the second conductive coating is formed by a printing method.

19. A light emitting device according to claim 13, wherein the switching element comprises at least one thin film transistor.

20. An electronic appliance comprising the light emitting device according to claim 13, wherein the light emitting device is selected from the group consisting of an electroluminescence display device, a personal computer, and a digital versatile disk.

21. A light emitting device comprising:

a plurality of pixels arranged in a matrix, each of the plurality of pixels comprising a switching element and a light emitting element;

a plurality of source signal lines for supplying signals to the switching element; and

at least one terminal,

wherein at least one of the plurality of source signal lines comprises a first conductor and a first conductive coating on the first conductor, and

wherein the terminal comprises a second conductor and a second conductive coating on the second conductor.

22. A light emitting device according to claim 21, wherein at least one of the first conductive coating and the third conductive coating is formed by an electroplating method.

23. A light emitting device according to claim 21, wherein at least one of the first and second conductive coating comprises at least one selected from the group consisting of Cu, Al, Au, Ag, and an alloy thereof as a main component.

sub A4

24. A light emitting device according to any one of claims 21, wherein the first conductor and the second conductor are simultaneously formed.

25. A light emitting device according to any one of claims 21, wherein at least one of the first conductive coating and the second conductive coating is made of the same material as a gate electrode of the switching element.

26. A light emitting device according to any one of claims 21, wherein at least one of the first conductive coating and the second conductive coating is formed by a printing method.

27. A light emitting device according to claim 21, wherein the switching element comprises at least one thin film transistor.

28. An electronic appliance comprising the light emitting device according to claim 21, wherein the light emitting device is selected from the group consisting of an electroluminescence display device, a personal computer, and a digital versatile disk.

29. A light emitting device comprising:

a plurality of pixels arranged in a matrix, each of the plurality of pixels comprising a switching element and a light emitting element;

a plurality of power supply lines for supplying potentials to the light emitting element; and

at least one terminal electrically connected to the plurality of power supply lines

wherein at least one of the plurality of power supply lines comprises a first conductor and a first conductive coating on the first conductor, and

wherein the terminal comprises a second conductor and a second conductive coating on the second conductor.

30. A light emitting device according to claim 29, wherein at least one of the first conductive coating and the second conductive coating is formed by an electroplating method.

31. A light emitting device according to claim 29, wherein at least one of the first conductive coating and the second conductive coating comprises at least one selected from the group consisting of Cu, Al, Au, Ag, and an alloy thereof as a main component

32. A light emitting device according to claim 29, wherein the first conductor and the second conductor are simultaneously formed.

33. A light emitting device according to claim 29, wherein at least one of the first conductive coating and the second conductive coating is made of the same material as a gate electrode of the switching element.

34. A light emitting device according to claim 29, wherein at least one of the first conductive coating and the second conductive coating is formed by a printing method.

35. A light emitting device according to claim 29, wherein the switching element comprises at least one thin film transistor.

36. An electronic appliance comprising the light emitting device according to claim 29, wherein the light emitting device is selected from the group consisting of an electroluminescence display device, a personal computer, and a digital versatile disk.

37. A light emitting device comprising:

a pixel portion comprising a plurality of pixels arranged in a matrix, each of the plurality of pixels comprising a first switching element, a plurality of source signal lines for supplying signals to the switching element, and a light emitting element; and

a driver circuit for driving the plurality of pixels, the driver circuit having a second switching element and a third switching element,

wherein at least one of the plurality of source signal lines comprises a conductor and a conductive coating on the conductor.

38. A light emitting device according to claim 37, wherein the first, second, and third switching elements are n-channel thin film transistors.

sub A5 39. A light emitting device according to claim 37, wherein the first, second, and third switching elements are a p-channel thin film transistors.

40. A light emitting device according to claim 37, wherein the second and third switching elements compose at least one of an EEMOS circuit and an EDMOS circuit.

41. A light emitting device according to claim 37, wherein the second switching element is an n-channel thin film transistor and the third switching element is a p-channel thin film transistor.

42. A light emitting device according to claim 37, wherein the conductive coating is formed by an electroplating method.

43. A light emitting device according to claim 37, wherein the conductive coating is formed by a printing method.

44. A light emitting device according to claim 37, wherein the conductive coating comprises at least one selected from the group consisting of Cu, Al, Au, Ag, and an alloy thereof as a main component.

45. A light emitting device according to claims 37, wherein the conductor is made of the same material as a gate electrode of the first, second, and third switching element.

46. A light emitting device according to claim 37, wherein at least one of the first, second, and third switching element comprises at least one tin film transistor.

47. A light emitting device according to claim 37, wherein the first switching element

comprises a plurality of channel forming regions.

48. A light emitting device according to claims 37, wherein the first switching element comprises three channel forming regions.

49. A light emitting device according to claim 37, wherein at least one of the first, second and third switching elements comprises a gate electrode having a taper portion, a channel forming region overlapped with the gate electrode, and an impurity region partially overlapped with the gate electrode.

50. A light emitting device according to claim 49, wherein the impurity region in at least one of the first, second, and third switching elements comprises a region having a concentration gradient at least at an impurity concentration of 1×10^{17} to 1×10^{18} /cm^3, and the impurity concentration is increased with increasing a distance from the channel forming region.

51. An electronic appliance comprising the light emitting device according to claim 37, wherein the light emitting device is selected from the group consisting of an electroluminescence display device, a personal computer, and a digital versatile disk.

52. A light emitting device comprising:

a pixel portion comprising a plurality of pixels arranged in a matrix, each of the plurality of pixels comprising a switching element, a light emitting element, and a plurality of power supply lines for supplying potentials to the light emitting element; and

a driver circuit for driving the plurality of pixels, the driver circuit having a second switching element and a third switching element,

wherein at least one of the plurality of power supply lines comprises a conductor and a conductive coating on the conductor.

53. A light emitting device according to claim 52, wherein at least one of the first, second, and third switching element comprises at least one thin film transistor.

54. A light emitting device according to claim 52, wherein the first, second, and third switching elements are n-channel thin film transistors.

sub A8 55. A light emitting device according to claim 52, wherein the first, second, and third switching elements are a p-channel thin film transistors.

56. A light emitting device according to claim 52, wherein the second and third switching elements compose at least one of an EEMOS circuit and an EDMOS circuit.

57. A light emitting device according to claim 52, wherein the second switching element is an n-channel thin film transistor and the third switching element is a p-channel thin film transistor.

58. A light emitting device according to claim 52, wherein the conductive coating is formed by an electroplating method.

59. A light emitting device according to claim 52, wherein the conductive coating is formed by a printing method.

60. A light emitting device according to claim 52, wherein the conductive coating comprises at least one selected from the group consisting of Cu, Al, Au, Ag, and an alloy thereof as a main component.

sub A9 61. A light emitting device according to claims 52, wherein the conductor is made of the same material as a gate electrode of the switching element.

62. A light emitting device according to claim 52, wherein the first switching element comprises a plurality of channel forming regions.

63. A light emitting device according to claims 52, wherein the first switching element comprises three channel forming regions.

64. A light emitting device according to claim 52, wherein at least one of the first, second and third switching elements comprises a gate electrode having a taper portion, a channel forming region overlapped with the gate electrode, and an impurity region partially overlapped with the gate electrode.

sub A10 65. A light emitting device according to claim 64, wherein the impurity region in at least one of the first, second, and third switching elements comprises a region having a concentration gradient at least at an impurity concentration of 1×10^{17} to 1×10^{18} /cm^3, and

the impurity concentration is increased with increasing a distance from the channel forming region.

66. An electronic appliance comprising the light emitting device according to claim 52, wherein the light emitting device is selected from the group consisting of an electroluminescence display device, a personal computer, and a digital versatile disk.

67. A method of manufacturing a light emitting device, comprising the steps of:

forming a semiconductor layer over an insulating surface of a substrate;

forming a gate insulating film over the semiconductor layer;

forming a gate electrode and a conductor over the gate insulating film;

adding an impurity element imparting an n-type to the semiconductor layer to form an n-type impurity region;

forming a conductive coating having a lower resistance than the conductor on a surface of the conductor by an electroplating method to form a source signal line;

forming an insulating film covering the source signal line; and

forming a gate signal line on the insulating film.

68. A method of manufacturing a light emitting device according to claim 67, wherein the source signal line is made of a material comprising at least one selected from the group consisting of Cu, Al, Au, Ag, and an alloy thereof as a main component.

69. A method of manufacturing a light emitting device according to any one of claim 67, wherein the conductor is connected with a wiring to be the same potential in the step using

the electroplating method.

70. A method of manufacturing a light emitting device according to claim 69, wherein the wiring is separated by a laser light after forming the conductive coating.

71. A method of manufacturing a light emitting device according to claim 69, wherein the wiring is separated simultaneously with the substrate after plating.

72. A method of manufacturing a light emitting device, comprising the steps of:

forming a semiconductor layer over an insulating surface of a substrate;

forming a gate insulating film over the semiconductor layer;

forming a gate electrode and a conductor over the gate insulating film;

adding an impurity element imparting an n-type to the semiconductor layer to form an n-type impurity region;

forming a conductive coating having a lower resistance than the conductor on a surface of the conductor by an electroplating method to form a power supply line;

forming an insulating film covering the power supply line; and

forming a gate signal line on the insulating film.

73. A method of manufacturing a light emitting device according to claim 72, wherein the source signal line is made of a material comprising at least one selected from the group consisting of Cu, Al, Au, Ag, and an alloy thereof as a main component.

74. A method of manufacturing a light emitting device according to any one of claim

sub A12 cont'd

72, wherein the conductor is connected with a wiring to be the same potential in the step using the electroplating method.

75. A method of manufacturing a light emitting device according to claim 74, wherein the wiring is separated by a laser light after forming the conductive coating.

76. A method of manufacturing a light emitting device according to claim 74, wherein the wiring is separated simultaneously with the substrate after plating.

add B37